

NTE2639 Silicon NPN Transistor CRT Horizontal Deflection, High Voltage, High Speed Switch

Description:

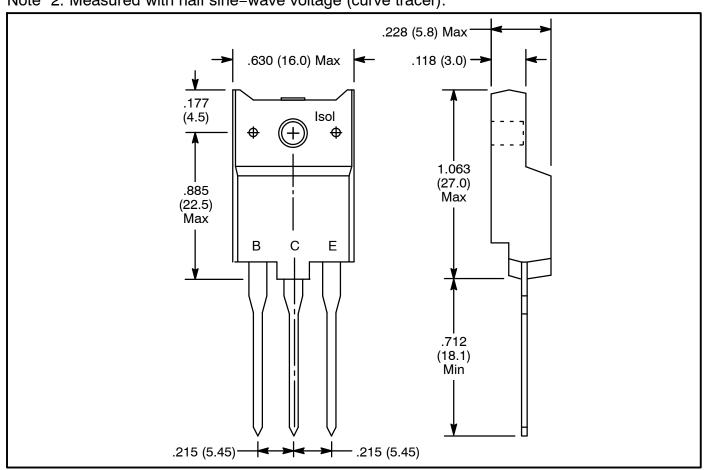
The NTE2639 is a high voltage, high speed switching silicon NPN transistor in a plastic full–pack envelope designed for use in horizontal deflection circuits of color TV receivers.

Absolute Maximum Ratings:
Collector–Emitter Voltage Peak Value (V _{BE} = 0V), V _{CESM}
Collector-Emitter Voltage (OpenBase), V _{CEO} 825V
Collector Current, I _C
DC
Base Current, I _B
DC
Peak Value
Reverse Base Current (Average over any 20ms period), $-I_{B(AV)}$
Reverse Base Current Peak Value (Note 1), -I _{BM}
Total Power Dissipation ($T_{HS} \le +25^{\circ}C$), P_{tot}
Electrostatic Discharge Capacitor Voltage (Human body model (250pF, 1.5kΩ), V _C 10kV
Operating Junction Temperature, T _J +150°C
Storage Temperature Range, T _{stg} 65° to +150°C
Maximum Thermal Resistance, Junction-to-Heatsink, RthJHS
Without Heatsink Compound
With Heatsink Compound
Typical Thermal Resistance, Junction-to-Ambient (In Free Air), R _{thJA}
Note 1. Turn-off current.

Electrical Characteristics: $(T_{HS} = +25^{\circ}C \text{ unless otherwise specified})$

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Isolation Limiting Value and Characteristic							
Repetitive Peak Voltage from All Three Terminals to External Heatsink	V _{isol}	R.H. ≤ 65%; Clean and Dustfree	-	_	2500	V	
Capacitance from T2 to External Heatsink	C _{isol}	f = 1MHz	_	22	_	pF	
Static Characteristics							
Collector Cutoff Current	I _{CES}	V _{CE} = 1700V, V _{BE} = 0	_	_	1.0	mA	
		$V_{CE} = 1700V, V_{BE} = 0, T_{J} = +125^{\circ}C$	_	_	2.0	mA	
Emitter Cutoff Current	I _{EBO}	V _{EB} = 7.5V, I _C = 0A	_	_	1.0	mA	
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _B = 1mA	7.5	13.5	_	V	
Collector-Emitter Sustaining Voltage	V _{CEO(sus)}	I _B = 0A, I _C = 100mA, L = 25mH	825	_	_	V	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = 7A, I _B = 1.75A	_	_	1.0	V	
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C = 7A, I _B = 1.75A	_	_	1.1	V	
DC Current Gain	h _{FE}	$V_{CE} = 5V, I_{C} = 0.1A$	_	22	_		
		V _{CE} = 1V, I _C = 7A	4.0	6.0	6.5		
Dynamic Characteristics (Switching Times, 16kHz Line Deflection Circuit)							
Turn-Off Storage Time	t _s	$\begin{array}{l} I_{C(sat)} = 7\text{A, } L_{C} = 650\mu\text{H, } C_{fb} = 18\text{nF,} \\ V_{CC} = 162\text{V, } I_{B(end)} = 1.5\text{A,} \\ L_{B} = 2\mu\text{H, } -\text{V}_{BB} = 4\text{V} \end{array}$	_	5.8	6.5	μs	
Turn-Off Fall Time	t _f	$L_{B} = 2\mu H, -V_{BB} = 4V$	_	0.6	0.8	μs	

Note 2. Measured with half sine-wave voltage (curve tracer).



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